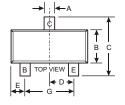
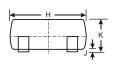


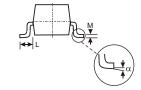
PNP SILICON EPITAXIAL PLANAR TRANSISTOR

Features

- For Switching and AF Amplifier Applications.
- Low Saturation Voltage.







SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
E	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
М	0.085	0.180			
α	0°	8°			
All Dimensions in mm					

Maximum Ratings @ T_A = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	-80	V
Collector Emitter Voltage	V_{CEO}	-80	٧
Emitter Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-500	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{Stg}	- 55 to + 150	°C

Electrical Characteristics @ TA = 25°C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breajdown voltage	V _{(BR)CBO}	I _C =-50μA,I _E =0	-80			V
Collector-emitter breajdown voltage	V _{(BR)CEO}	I _C =-2mA,I _B =0	-80			V
Emitter-base breajdown voltage	V _{(BR)EBO}	I _E =-50μA,I _C =0	-5			V
Collector cut-off current	Ісво	V _{CB} =-50V,I _E =0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V,I _C =0			-0.5	μΑ
DC current gain	h _{FE}	V _{CE} =-3V,I _C =-100mA	120		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA,I _B =-50mA			-0.5	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		11		pF
Transition frequency	f⊤	V _{CE} =-10V, I _C =-50mA, f=100MHz		180		MHz

CLASSIFICATION OF hFE

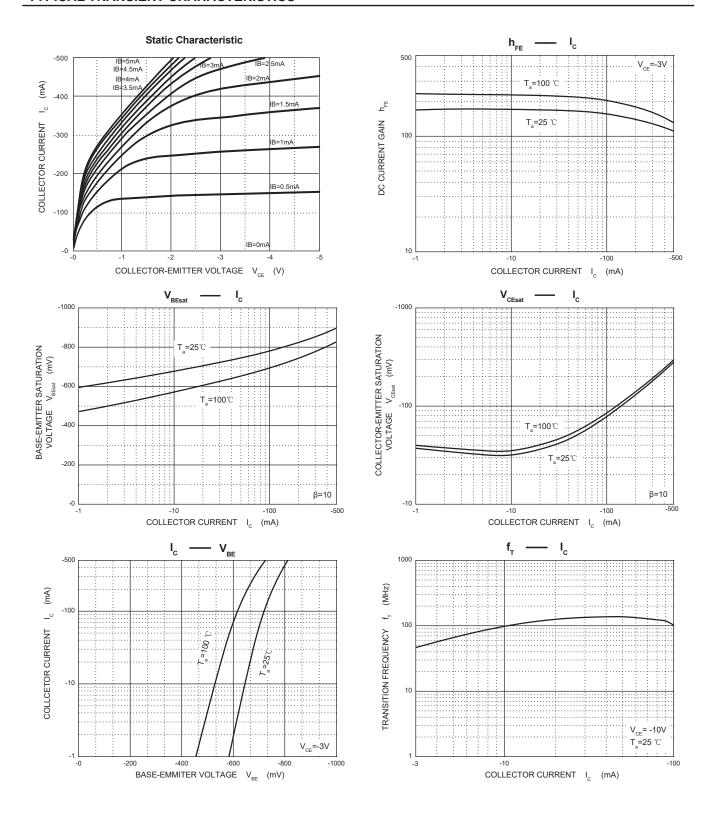
Rank	Q	R
Range	120-270	180-390
MARKING	AKQ	AKR





PNP SILICON EPITAXIAL PLANAR TRANSISTOR

TYPICAL TRANSIENT CHARACTERISTICS







PNP SILICON EPITAXIAL PLANAR TRANSISTOR

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